

HIGH-POWER PNP SILICON POWER TRANSISTORS

...designed for use in general-purpose amplifier and switching application

FEATURES:

- * Recommend for 150W High Fidelity Audio Frequency Amplifier Output stage
- * Complementary to 2SC3858

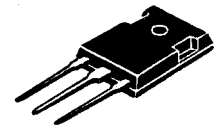
PNP
2SA1494

17 AMPERE
POWER
TRANSISTOR

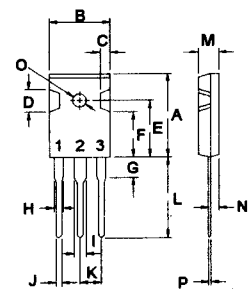
200 VOLTS
200 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	2SA1494	Unit
Collector-Emitter Voltage	V_{CEO}	200	V
Collector-Base Voltage	V_{CBO}	200	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous - Peak	I_C I_{CM}	17 20	A
Base current	I_B	2.0	A
Total Power Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	200 1.6	W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$



TO-247(3P)



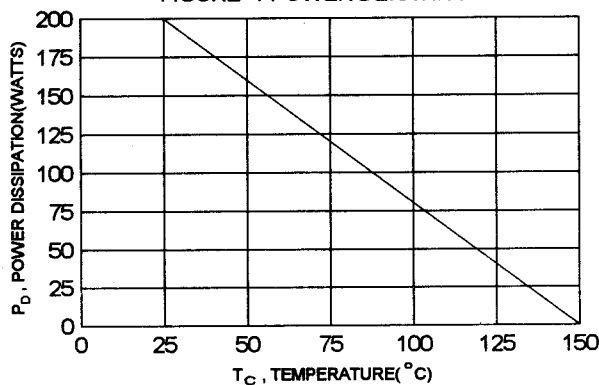
PIN 1.BASE
2.COLLECTOR
3.EMITTER

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.625	$^\circ C/W$

DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70

FIGURE -1 POWER DERATING



ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 50\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	200		V
Collector Cutoff Current ($V_{CB} = 200\text{ V}$, $I_E = 0$)	I_{CBO}		100	μA
Emitter Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	I_{EBO}		100	μA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 8.0\text{ A}$, $V_{CE} = 4.0\text{ V}$)	hFE	30		
Collector-Emitter Saturation Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$)	$V_{CE(sat)}$		2.5	V

DYNAMIC CHARACTERISTICS

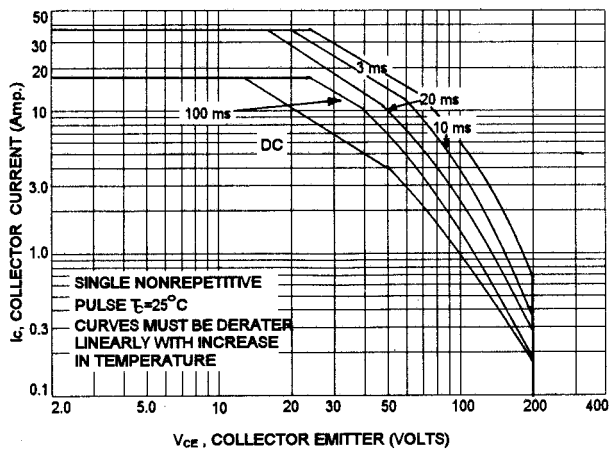
Current-Gain-Bandwidth Product ($I_C = 1.0\text{ A}$, $V_{CE} = 12\text{ V}$, $f = 1.0\text{ MHz}$)	f_T	10		MHz
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SWITCHING CHARACTERISTICS

Turn-on Time	$V_{CC} = 40\text{ V}$, $I_C = 10\text{ A}$ $I_{B1} = -I_{B2} = 1.0\text{ A}$ $R_L = 4.0\text{ ohm}$	t_{on}	0.60(typ)		μs
Storage Time		t_s	0.90(typ)		μs
Fall Time		t_f	0.30(typ)		μs

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

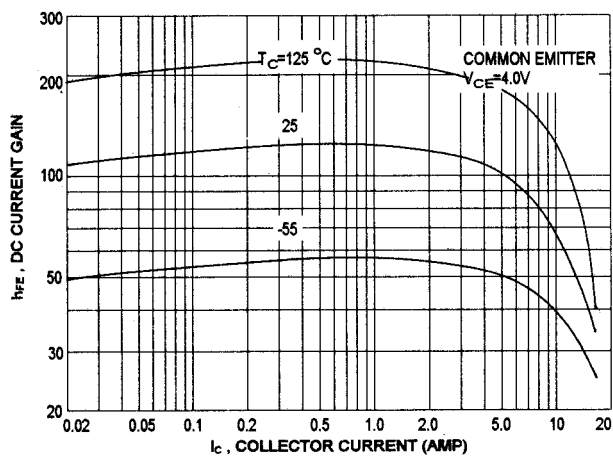
ACTIVE-REGION SAFE OPERATING AREA (SOA)



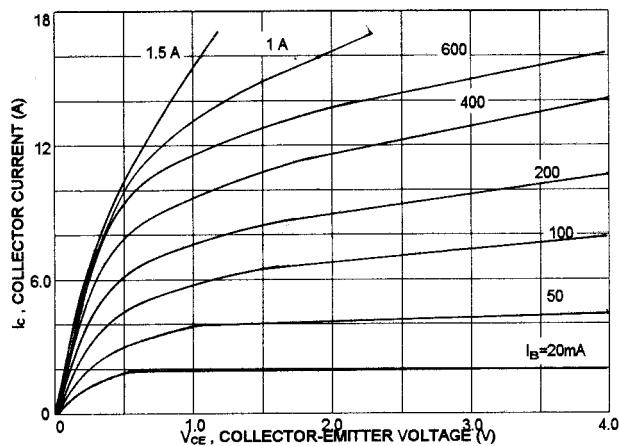
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)}=150^\circ\text{C}$; T_c is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

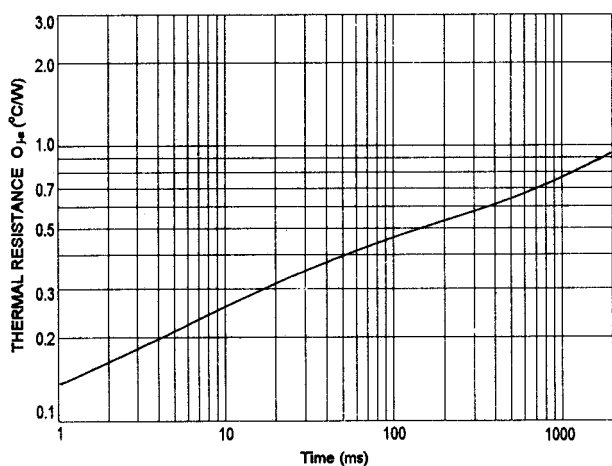
DC CURRENT GAIN



$I_C - V_{CE}$



$\theta_{ja} - t$



$V_{CE(sat)} - I_B$

